TIP120, TIP121, TIP122 (NPN); TIP125, TIP126, TIP127 (PNP)

Plastic Medium-Power Complementary Silicon Transistors

Designed for general−purpose amplifier and low−speed switching applications.

Features

- High DC Current Gain −
  h_{FE} = 2500 (Typ) @ I_C
  = 4.0 Adc
- Collector−Emitter Sustaining Voltage − @ 100 mAdc
  $V_{CEO(sus)}$ = 60 Vdc (Min) − TIP120, TIP125
  = 80 Vdc (Min) − TIP121, TIP126
  = 100 Vdc (Min) − TIP122, TIP127
- Low Collector−Emitter Saturation Voltage −
  $V_{CE(sat)}$ = 2.0 Vdc (Max) @ I_C = 3.0 Adc
  = 4.0 Vdc (Max) @ I_C = 5.0 Adc
- Monolithic Construction with Built−In Base−Emitter Shunt Resistors
- Pb−Free Packages are Available*

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor®

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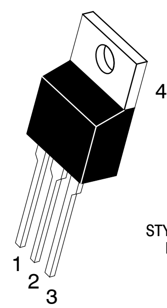
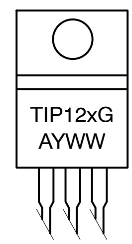
DARLINGTON
5 AMPERE
COMPLEMENTARY SILICON
POWER TRANSISTORS
60−80−100 VOLTS, 65 WATTS



TO−220AB
CASE 221A
STYLE 1

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

MARKING DIAGRAM



TIP12x	= Device Code
x	= 0, 1, 2, 5, 6, or 7
A	= Assembly Location
Y	= Year
WW	= Work Week
G	= Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	TIP120, TIP125	TIP121, TIP126	TIP122, TIP127	Unit
Collector–Emitter Voltage	V_{CEO}	60	80	100	Vdc
Collector–Base Voltage	V_{CB}	60	80	100	Vdc
Emitter–Base Voltage	V_{EB}	5.0			Vdc
Collector Current – Continuous – Peak	I_C	5.0 8.0			Adc
Base Current	I_B	120			mAdc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	65 0.52			W W/°C
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	2.0 0.016			W W/°C
Unclamped Inductive Load Energy (Note 1)	E	50			mJ
Operating and Storage Junction, Temperature Range	T_J, T_{stg}	–65 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	1.92	°C/W
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	62.5	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I_C = 1 A, L = 100 mH, P.R.F. = 10 Hz, V_{CC} = 20 V, R_{BE} = 100 Ω

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 2) (I_C = 100 mAdc, I_B = 0)	TIP120, TIP125 TIP121, TIP126 TIP122, TIP127	$V_{CEO(sus)}$	60 80 100	– – –	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, I_B = 0) (V_{CE} = 40 Vdc, I_B = 0) (V_{CE} = 50 Vdc, I_B = 0)	TIP120, TIP125 TIP121, TIP126 TIP122, TIP127	I_{CEO}	– – –	0.5 0.5 0.5	mAdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 80 Vdc, I_E = 0) (V_{CB} = 100 Vdc, I_E = 0)	TIP120, TIP125 TIP121, TIP126 TIP122, TIP127	I_{CBO}	– – –	0.2 0.2 0.2	mAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)		I_{EBO}	–	2.0	mAdc
ON CHARACTERISTICS (Note 2)					
DC Current Gain (I_C = 0.5 Adc, V_{CE} = 3.0 Vdc) (I_C = 3.0 Adc, V_{CE} = 3.0 Vdc)		h_{FE}	1000 1000	– –	–
Collector–Emitter Saturation Voltage (I_C = 3.0 Adc, I_B = 12 mAdc) (I_C = 5.0 Adc, I_B = 20 mAdc)		$V_{CE(sat)}$	– –	2.0 4.0	Vdc
Base–Emitter On Voltage (I_C = 3.0 Adc, V_{CE} = 3.0 Vdc)		$V_{BE(on)}$	–	2.5	Vdc
DYNAMIC CHARACTERISTICS					
Small–Signal Current Gain (I_C = 3.0 Adc, V_{CE} = 4.0 Vdc, f = 1.0 MHz)		h_{fe}	4.0	–	–
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 0.1 MHz	TIP125, TIP126, TIP127 TIP120, TIP121, TIP122	C_{ob}	– –	300 200	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%

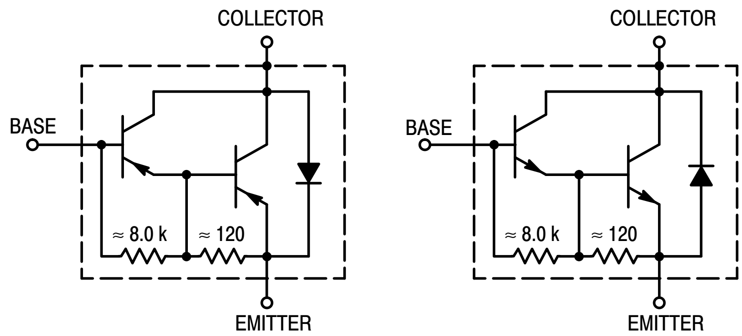


Figure 1. Darlington Circuit Schematic

ORDERING INFORMATION

Device	Package	Shipping
TIP120	TO−220	50 Units / Rail
TIP120G	TO−220 (Pb−Free)	50 Units / Rail
TIP121	TO−220	50 Units / Rail
TIP121G	TO−220 (Pb−Free)	50 Units / Rail
TIP122	TO−220	50 Units / Rail
TIP122G	TO−220 (Pb−Free)	50 Units / Rail
TIP125	TO−220	50 Units / Rail
TIP125G	TO−220 (Pb−Free)	50 Units / Rail
TIP126	TO−220	50 Units / Rail
TIP126G	TO−220 (Pb−Free)	50 Units / Rail
TIP127	TO−220	50 Units / Rail
TIP127G	TO−220 (Pb−Free)	50 Units / Rail

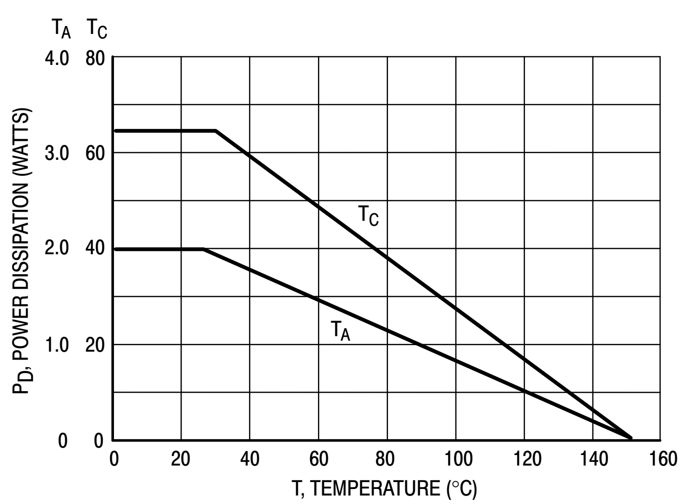


Figure 2. Power Derating

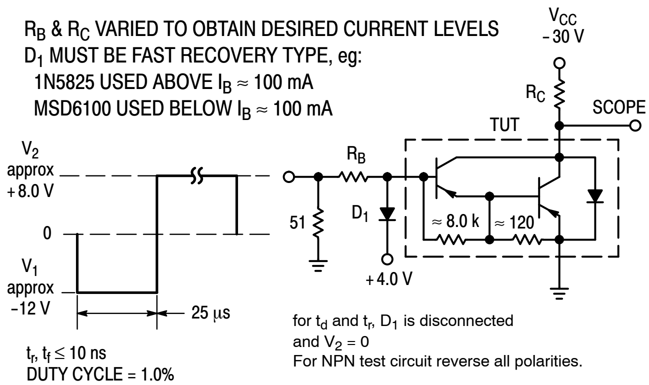


Figure 3. Switching Times Test Circuit

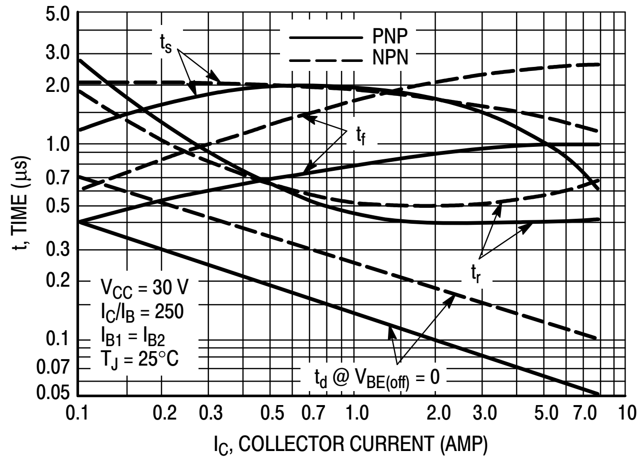


Figure 4. Switching Times

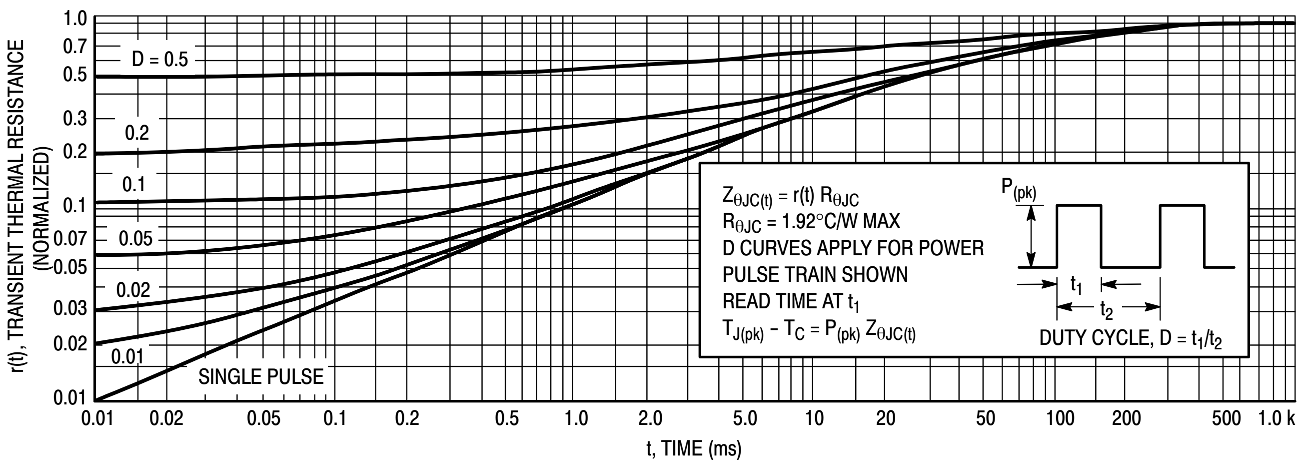


Figure 5. Thermal Response

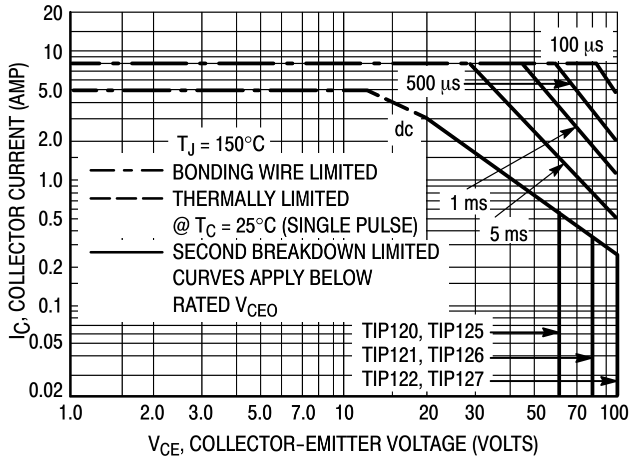


Figure 6. Active−Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)}$ = 150°C; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)}$ < 150°C. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown

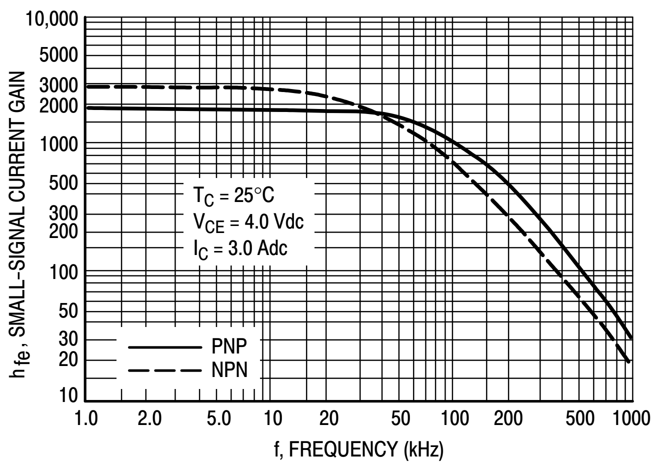


Figure 7. Small−Signal Current Gain

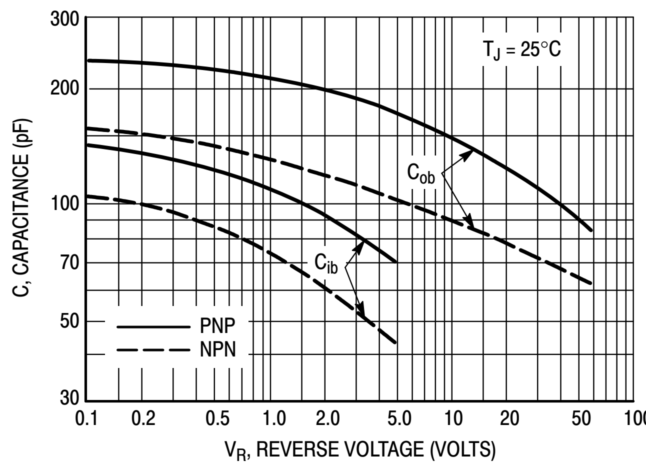


Figure 8. Capacitance

NPN
TIP120, TIP121, TIP122

PNP
TIP125, TIP126, TIP127

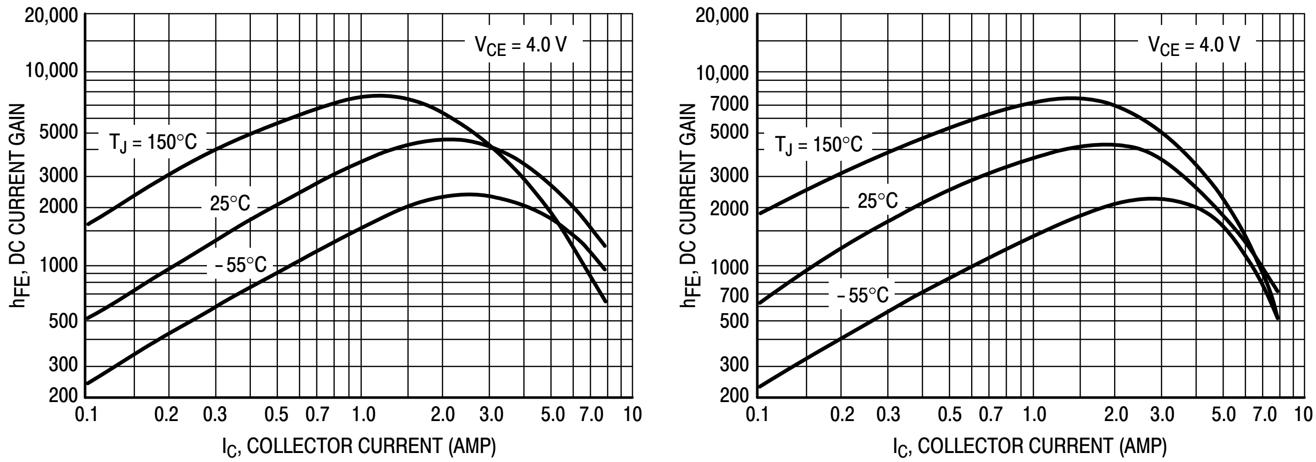


Figure 9. DC Current Gain

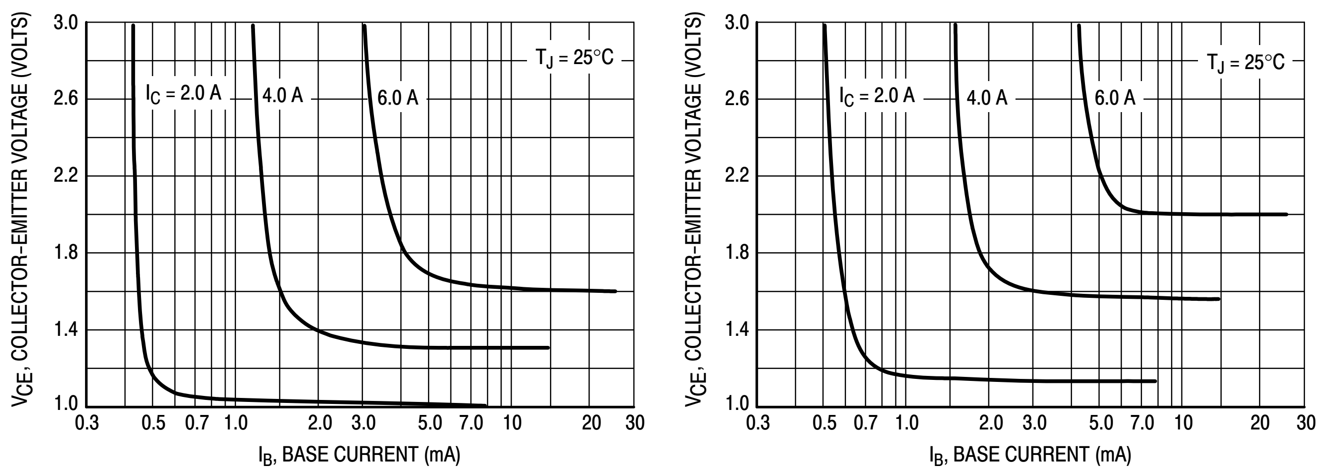


Figure 10. Collector Saturation Region

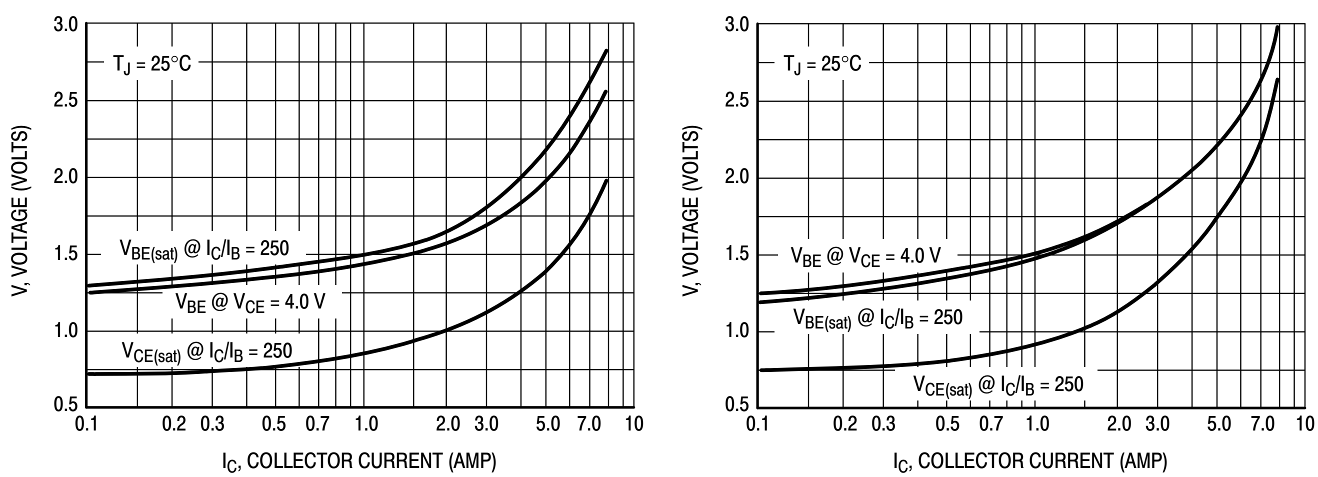


Figure 11. "On" Voltages

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
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